

Saras Embedded STile™ IPD Technology for High Performance Power Delivery Networks

Bart DeProspo
Director of Product Management

Outline

- Company Introduction
- Power Challenges
- Proposed Solutions
- Saras STile Solution
- Summary and Conclusions

Saras Micro Devices

To be the leading supplier of advanced power delivery solutions for leading AI/ML, HPC, & network systems



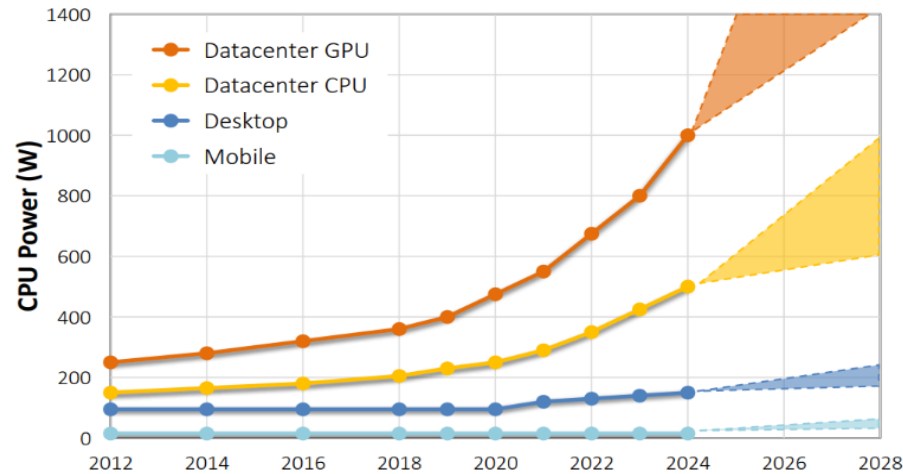
Manufacturing COE and HQ (Chandler, AZ)



R&D COE (Atlanta, GA)

Power Problem

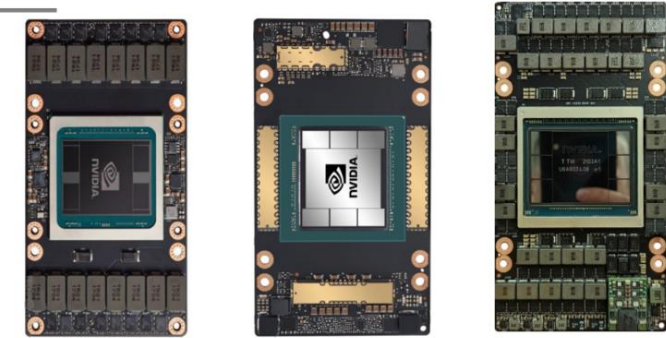
Microprocessor Power Trends



Source: Intel 2024¹

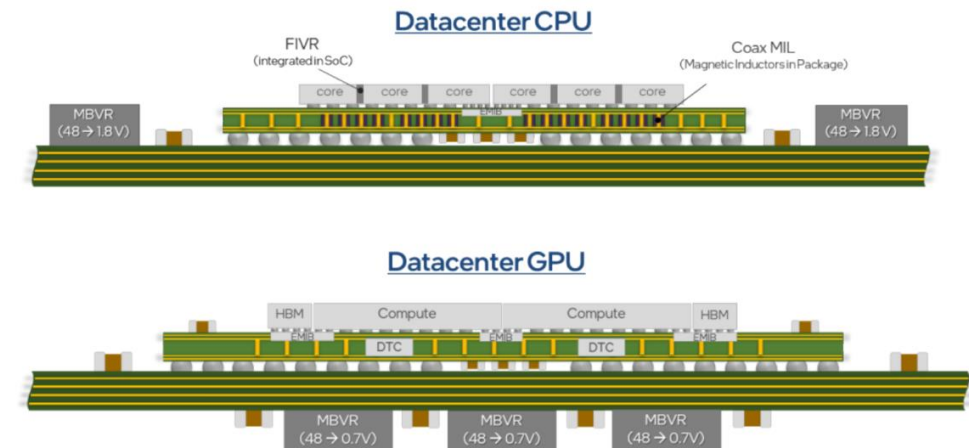
- ▶ Increasing Power and Current Density
- ▶ Rising I^2R losses due to higher I and lower V
- ▶ Reduced space for package level Caps

Evolution of High-Performance GPUs



	V100 (Volta)	A100 (Ampere)	H100 (Hopper)
Release year	2017	2020	2023
Power (W)	300W	500W	700W
Vin (V)	12	48	48

PD Architecture – CPU vs. GPU



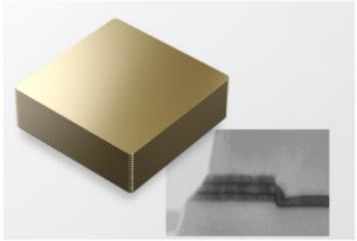
Source: nVidia 2024²

Proposed Solutions

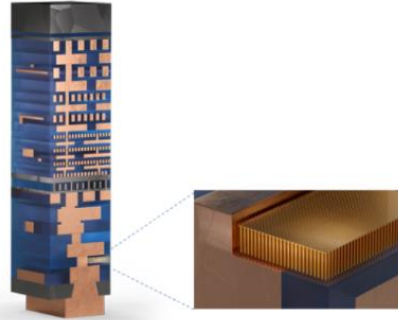
On Chip

Capacitor Technologies

SuperMIM (Planar MIM Technology)



Intel 18A with PowerVIA & HDMIM Technology



- Significant improvements over the years in on-die MIM technology
 - Newly introduced HDMIM technology can enable 500nF/mm² for each capacitor layer

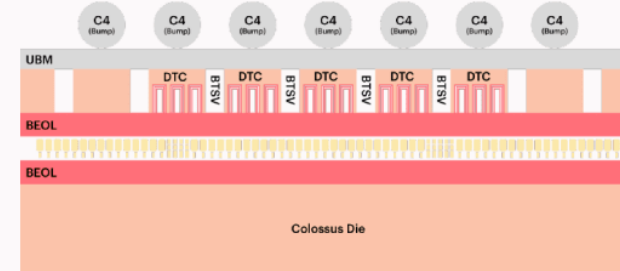
Source: Intel³

- ▶ On Chip Back-Side Power Delivery
- ▶ Focus on Capacitor integration with Silicon

Package Level

BOW IPU - 3D WAFER ON WAFER PROCESSOR

GRAPHCORE + 



Advanced silicon wafer stacking technology co-developed between Graphcore and TSMC

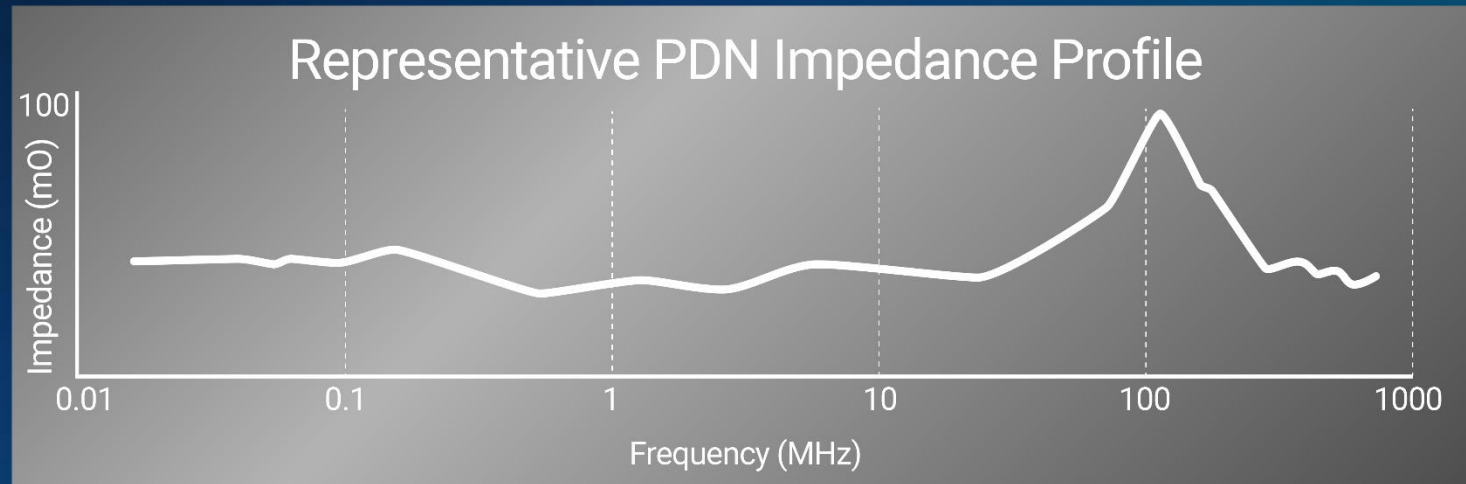
World's first commercial deployment using TSMC SoIC-WoW™ technology in BOW IPU

Enabling technology for closely coupled power delivery die to maximize application performance

Source: TSMC⁴

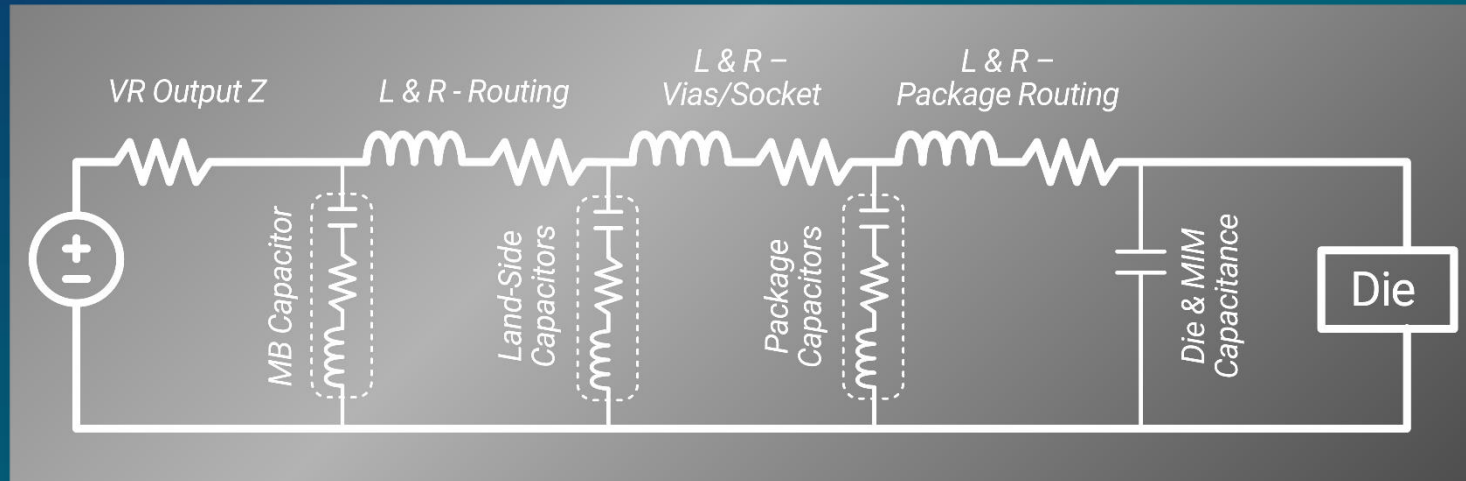
- ▶ Silicon DTC Interposer
- ▶ Embedded IPD's in Silicon

Today's PDN Approach



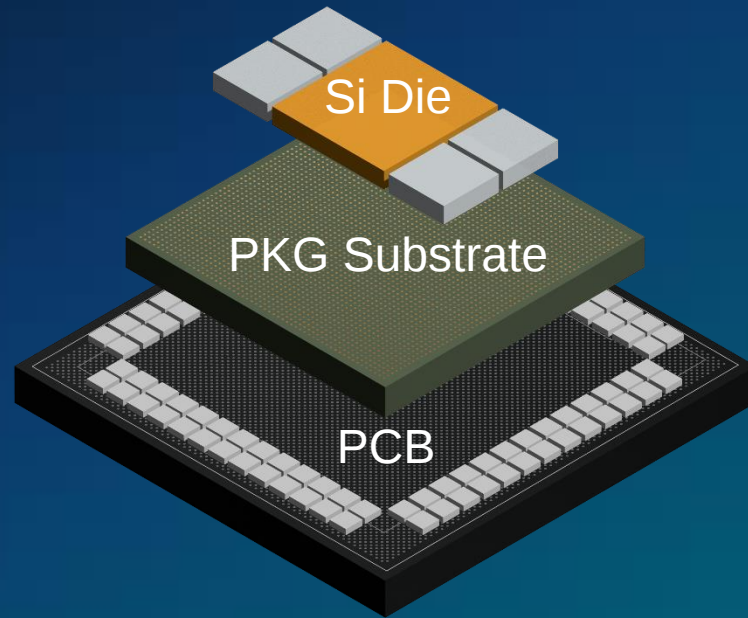
PDN Challenges:

- ▶ Design Complexity
- ▶ PDN Losses
- ▶ Increase in Total Number of Discretes

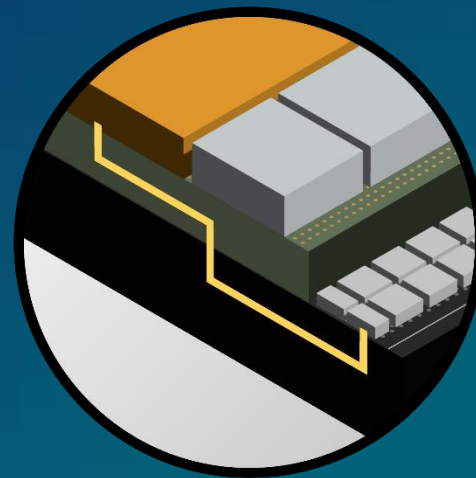


Saras STile™ Technology

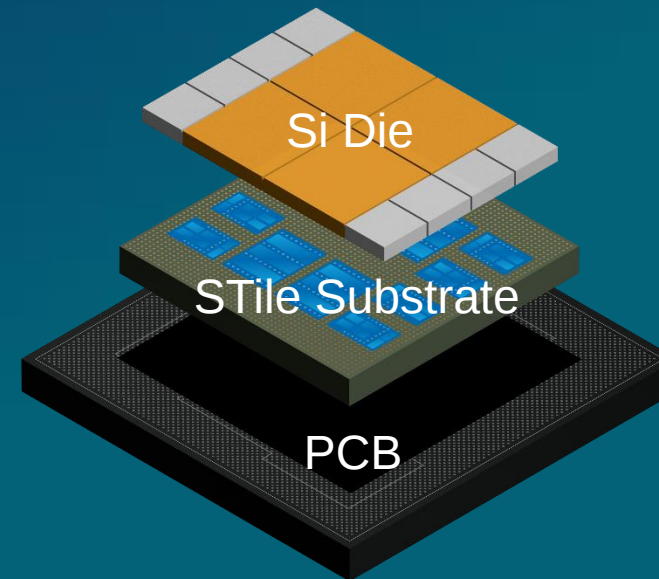
CURRENT STATE State of Art



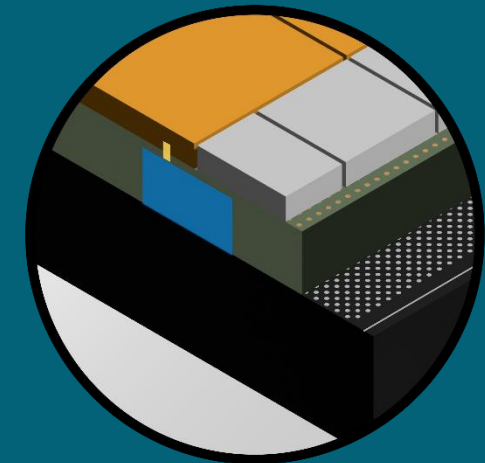
- ▶ Hundreds of Passives Required
- ▶ Long power path routing lengths
- ▶ Rising Si to Package Area Ratio



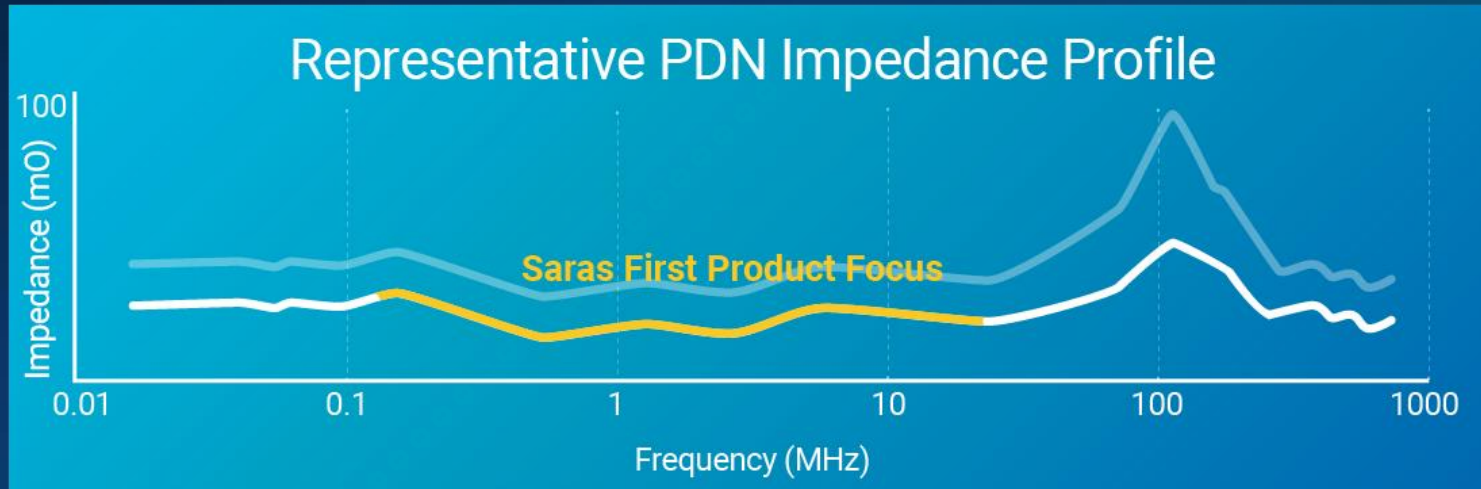
saras TILE



- ▶ Function Specific STiles
- ▶ Vertical Power Deliver
- ▶ No Limitation from Passive Components

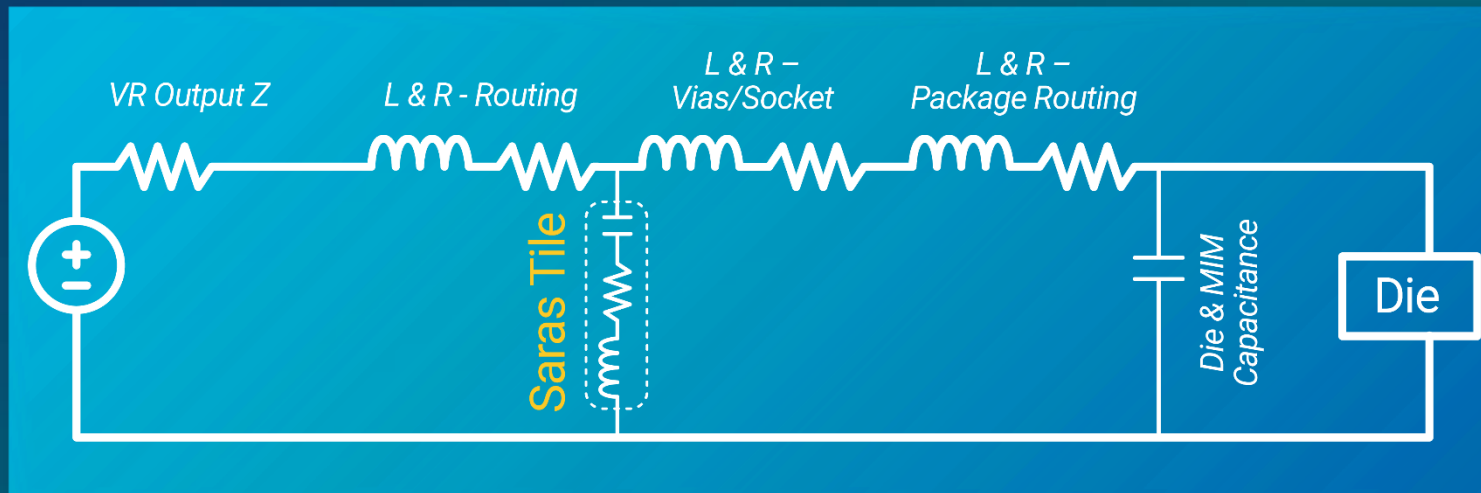


Product Application Focus

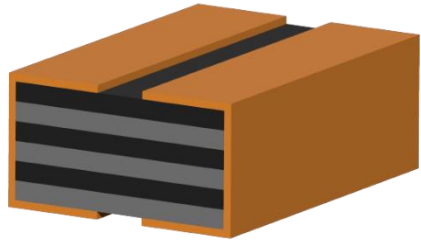


STile PDN Benefits

- Design Simplicity
- Higher Performance
- Larger Area Real Estate for Silicon



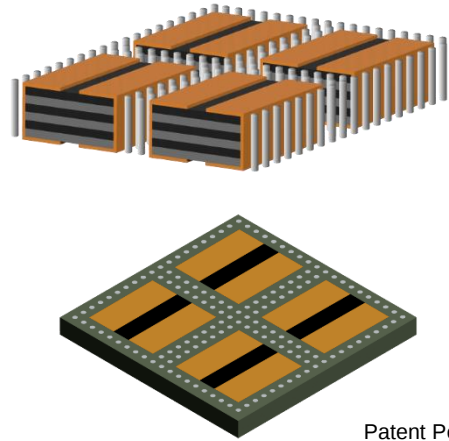
Saras Product Offerings



Capacitor Element

- ▶ Stacked Capacitive Element
- ▶ Formfactor and Performance Customizability

Development 2023

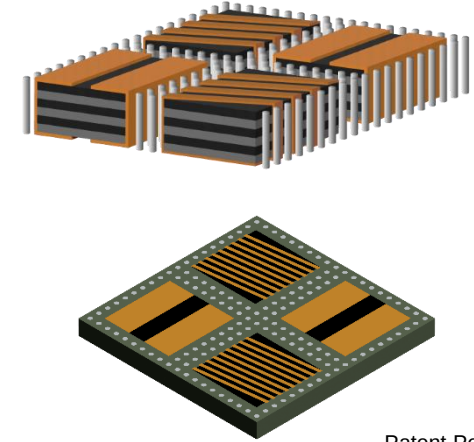


Patent Pending

STile™ Technology

- ▶ Multi-domain Capacitor
- ▶ Single Integrated Device

Product 2024



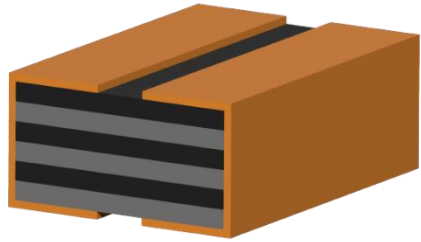
Patent Pending

Integrated Voltage Regulator

- ▶ Integration of L + C
- ▶ Enable advanced PDN Roadmap

Introduce 2025

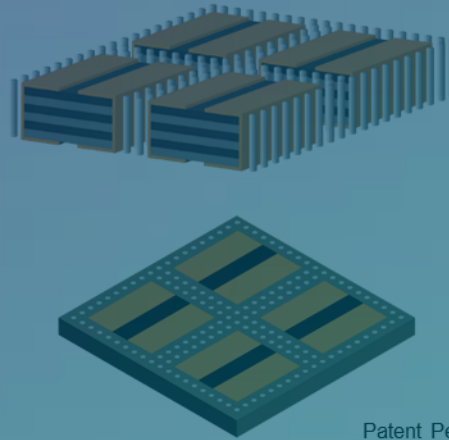
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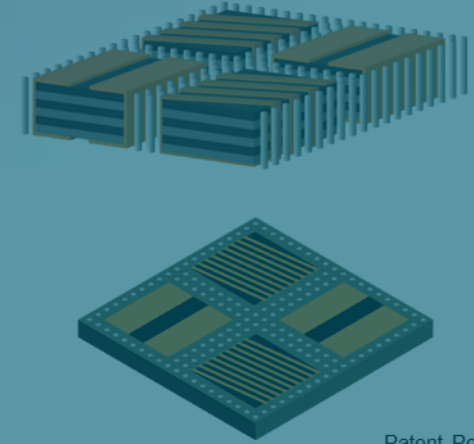


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- ▶ Multi-domain Package Capacitor
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Product 2024



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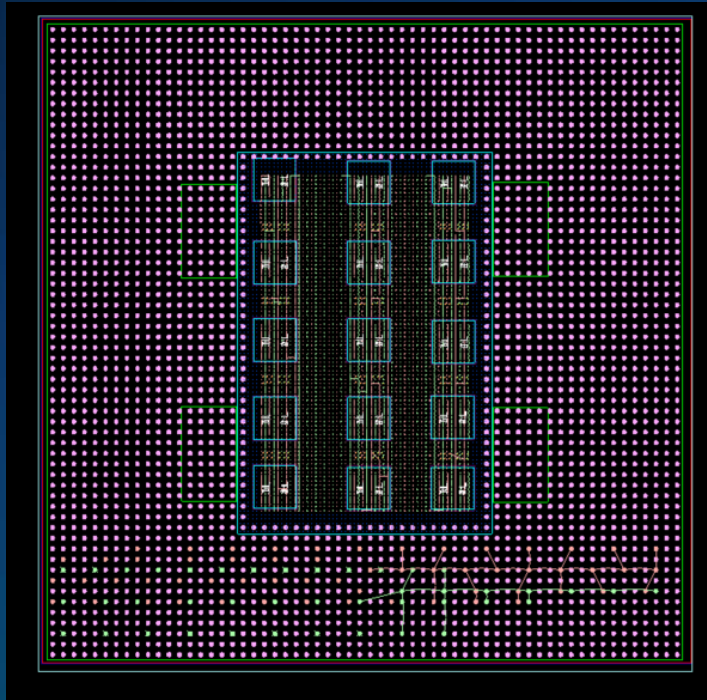
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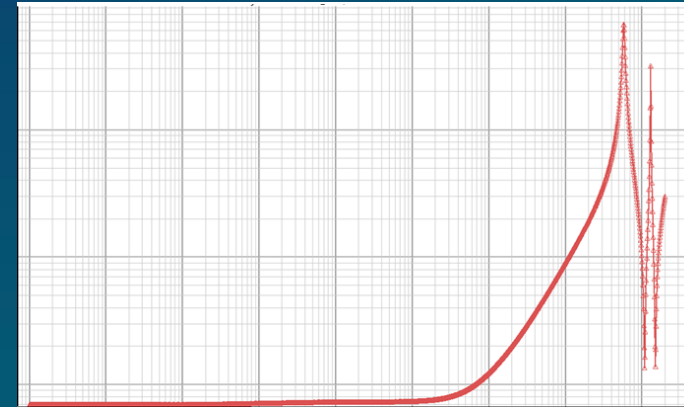
Device Performance

Capacitive Cell Size Examples		Cell A	Cell B	Comment
Dimension XY (mm)		4.0 x 4.0	4.0 x 7.0	Additional customization available upon request
Min. Capacitance (uF) @ 100kHz	800 µm high	24 - 64	42 - 112	1.5 µF/mm ² – 4.0 µF/mm ² . Higher Density on Request
	1000 µm high	32 - 72	56 - 126	2.0 µF/mm ² – 4.5 µF/mm ² . Higher Density on Request
	1200 µm high	40 - 80	70 - 140	2.5 µF/mm ² – 5.0 µF/mm ² . Higher Density on Request
R _s @ 100 KHz (mΩ)		15	15	Maximum ESR
ESR @ S.R.F. (mΩ)		10	10	Maximum ESR
Frequency Range		<30 MHz		Dictated by Resonance
Operating Temperature Range		0°C – 125°C		
Capacitance Variation versus Temperature		<10%		Preliminary Reliability Data
Rated Voltage		4V		Higher RV possible
Capacitance Variation versus RVDC		<5%		Limited Test Data Available

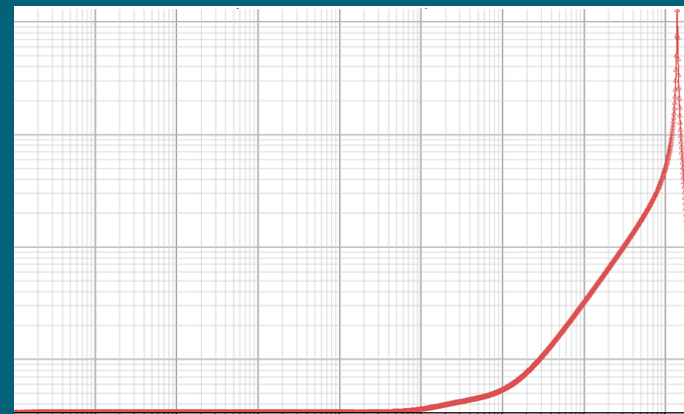
System Level Model | Preliminary



SIEMENS



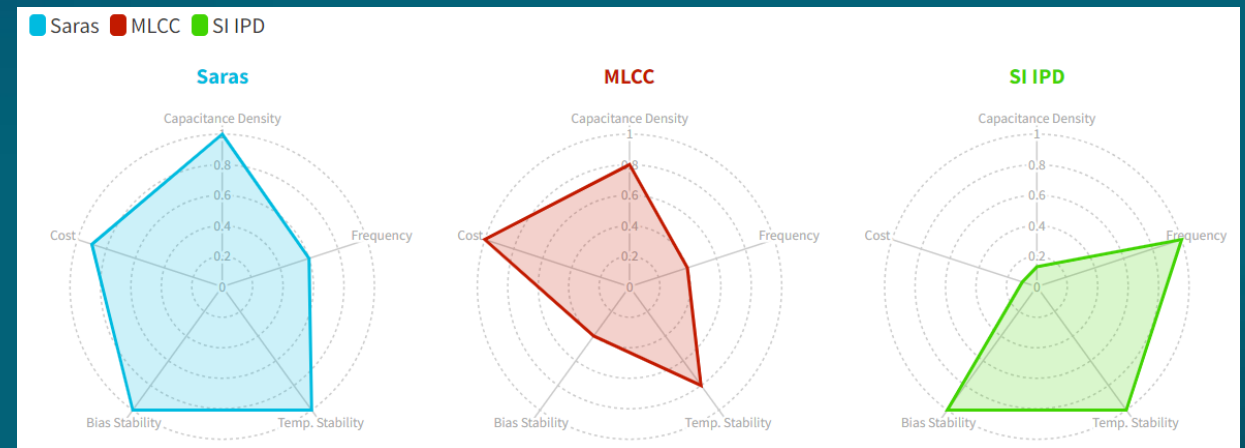
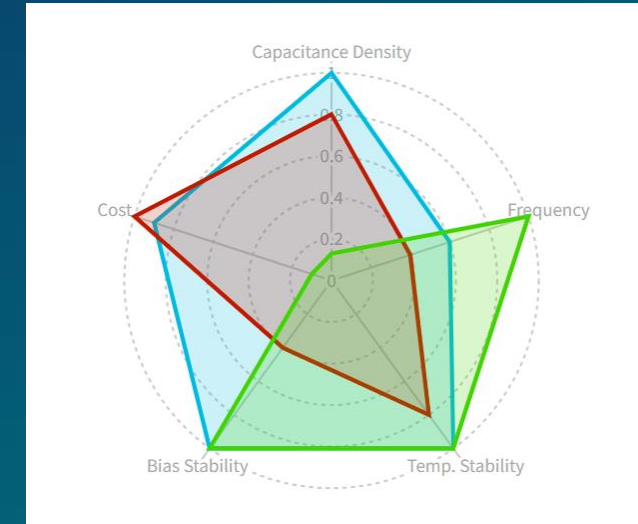
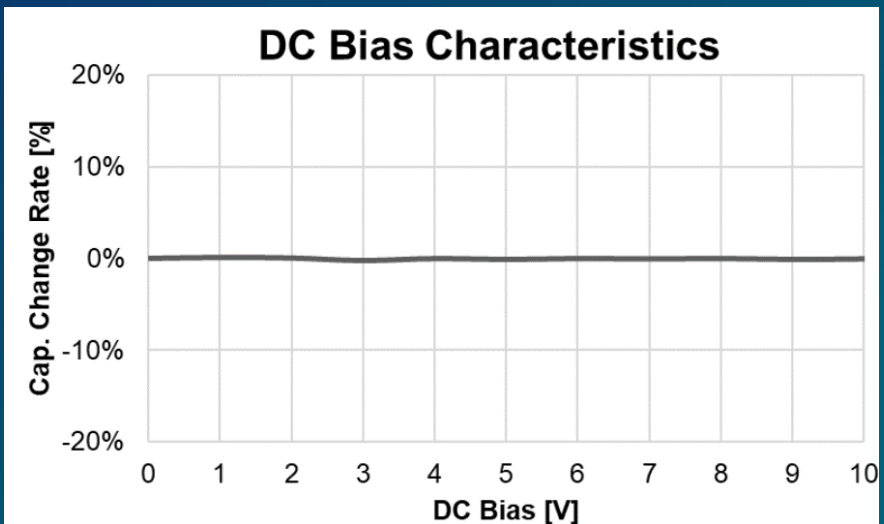
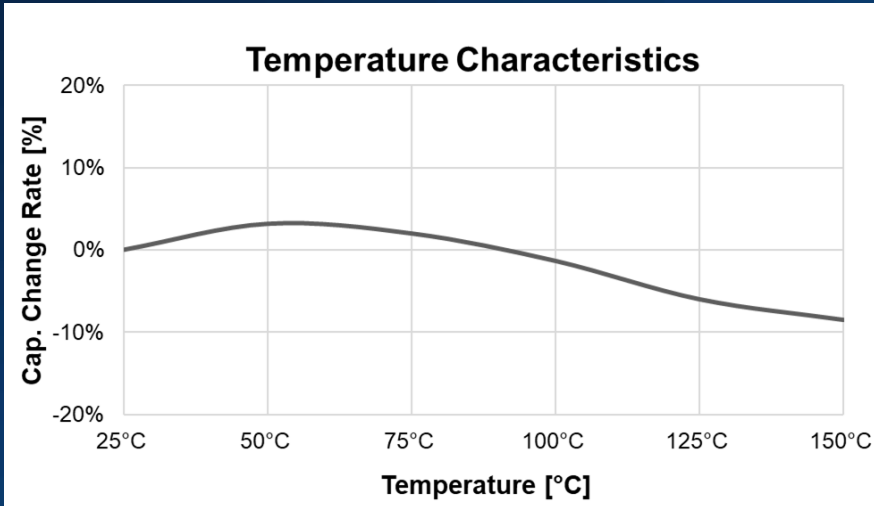
► No embedded STile™



► With Embedded STile™

48% Reduction in System Level |Z|

STile Stability and Positioning



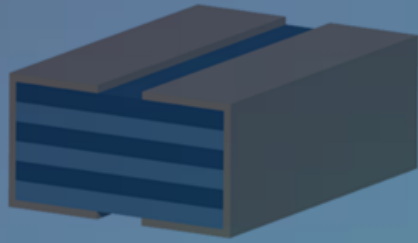
Saras Capacitor Temperature and Bias Stability superior to MLCC

Capacitor Reliability Testing

Test	Test Conditions	Test Targets	Test Duration	Results
HTS	150°C	500 Hours	500 Hours	<10% Change in C_s/R_s
Bias Test	4V @ 105°C	150 Hours	720 Hours	<10% Change in C_s/R_s
TCG	-40°C to 125°C	1000 Cycles	1200 Cycles	<5% Change in C_s/R_s
T/H-1	85°C / 85% RH	500 Hours	1000 Hours	<10% Change in C_s/R_s
T/H-2	110°C / 85% RH	100 Hours	800 Hours	<5% Change C_s/R_s
bHAST	4V @ 110°C / 85% RH	24 Hours	48 Hours	<5% Change in C_s/R_s

- Capacitor stability through extended reliability test conditions

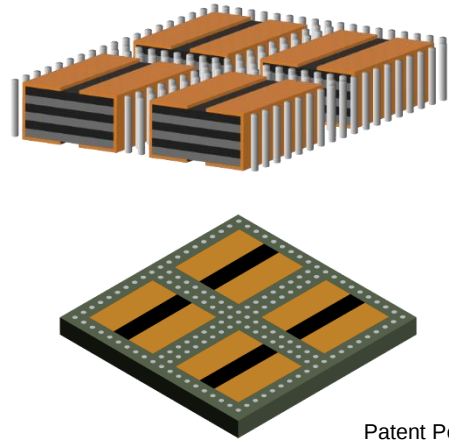
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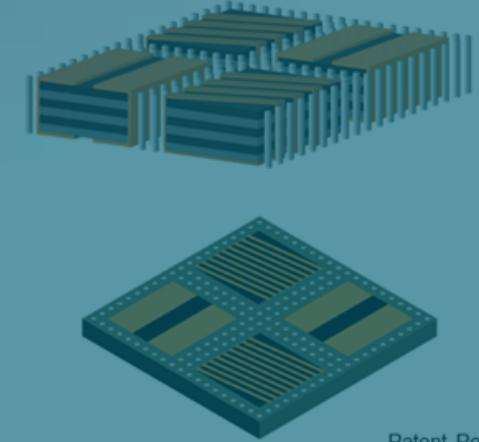


Patent Pending

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Product 2024



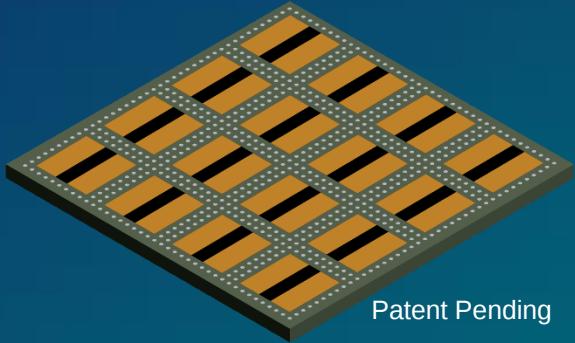
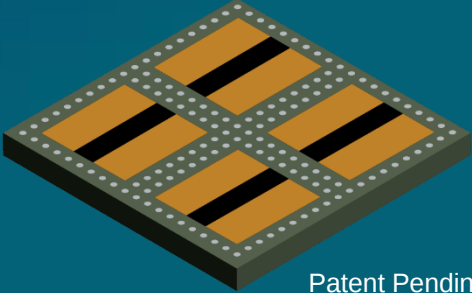
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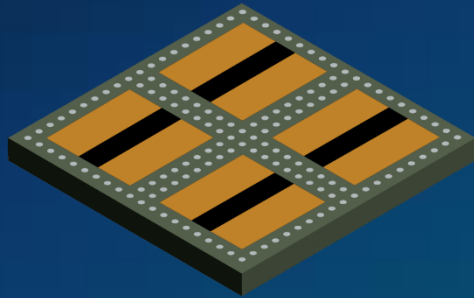
Introduce 2025

Saras Development STiles™

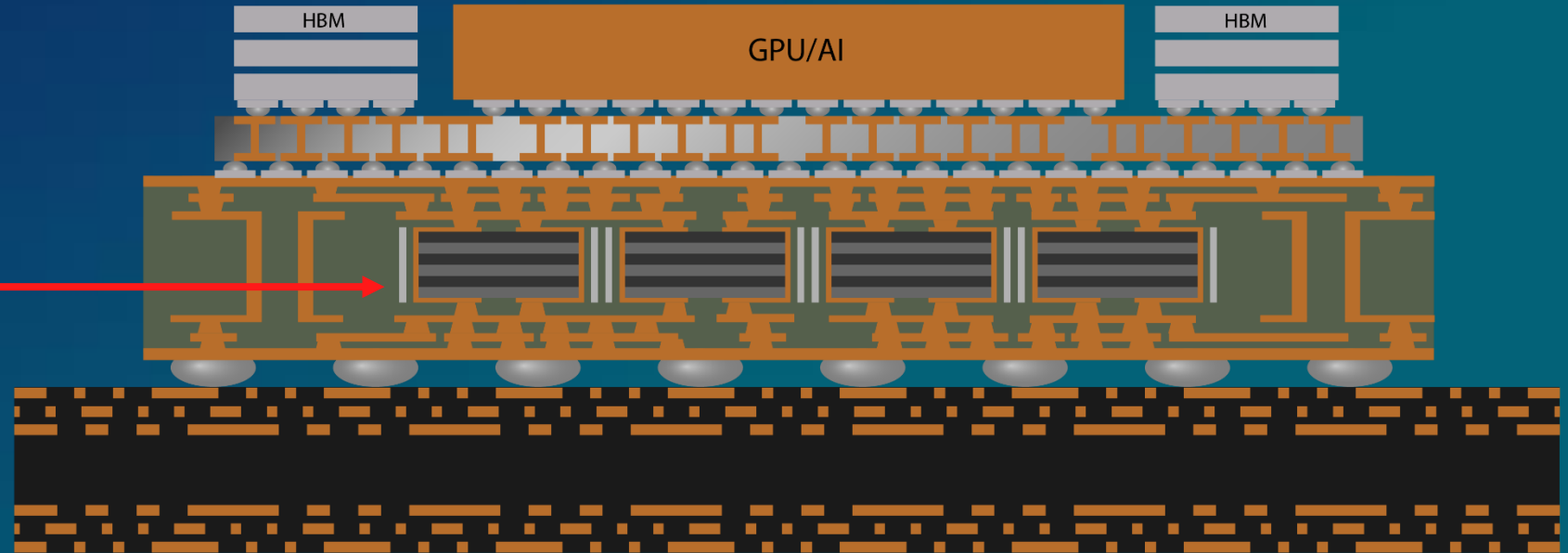
	Saras TV1.1  Patent Pending	Saras TV1.2  Patent Pending
Tile Size (mm)	21 x 21 x 1.2	11 x 11 x 1.2
Total Cap Domains	16 (4x4 mm cap domains)	4 (4x4 mm cap domains)
Total Capacitance (μF)	640 - 1,280	160 - 320
Number of Thru Vias	1472	240

- Non-uniform Capacitor Sizing Possible

Package / System Integration Options

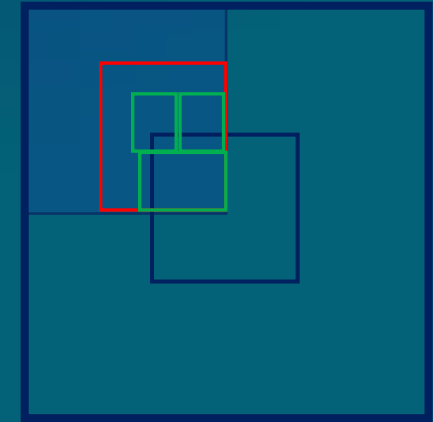
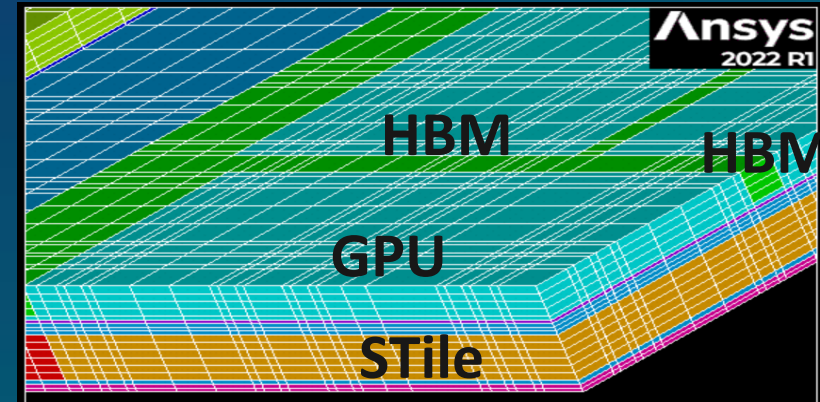
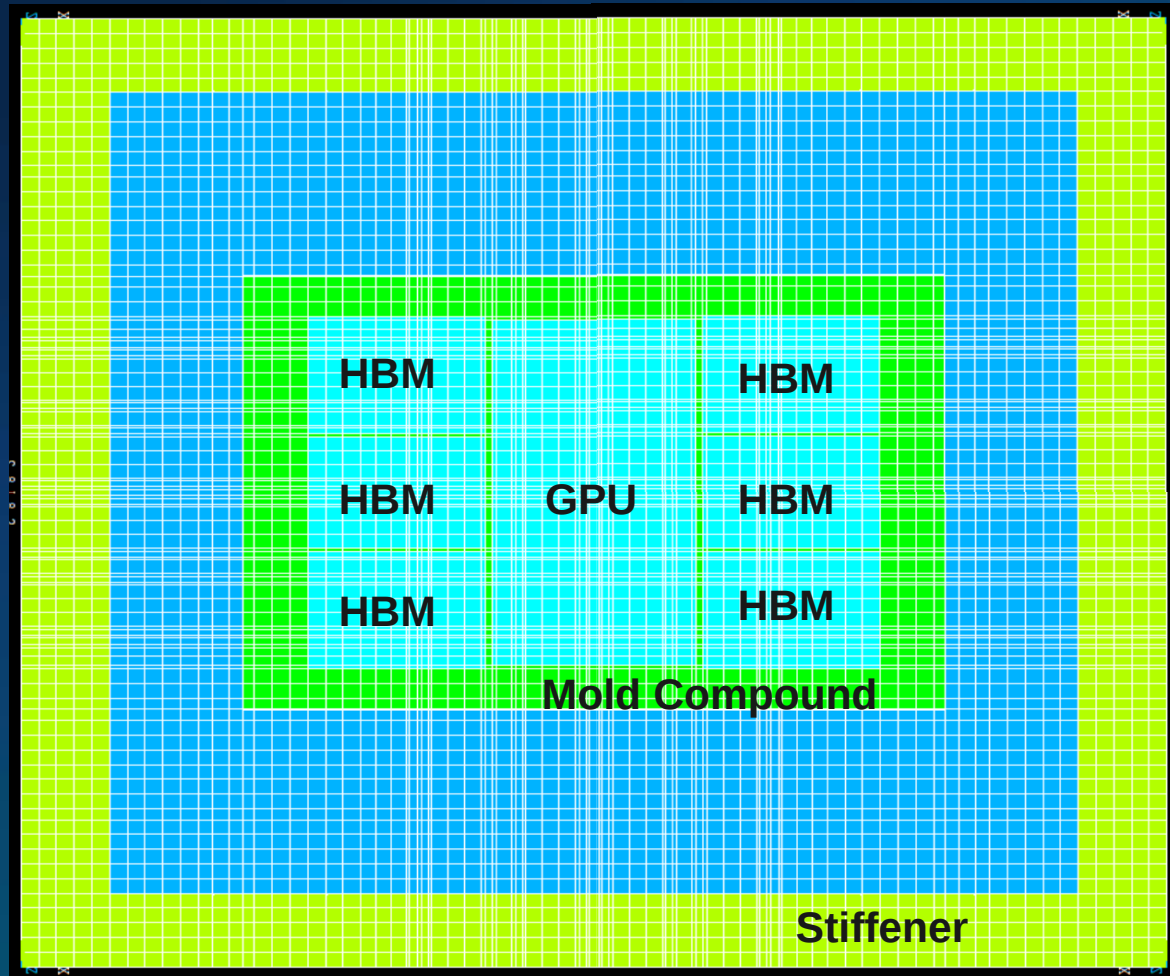


Patent Pending



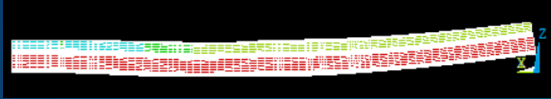
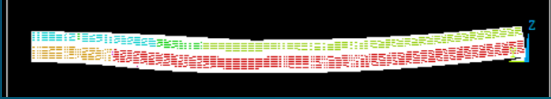
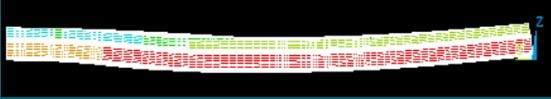
- ▶ Primary Development focus to embed STiles inside of the Organic Package Substrate
- ▶ Alternative embedding options available
- ▶ Pass through Via's ensure sufficient DC return paths

Thermomechanical Modeling Setup



- ▶ Impact of embedded STile on Substrate
- ▶ ANSYS FEA Analysis on embedded STile Devices
- ▶ How does the Package Behave during Reflow?

Modeling Results

Conditions	No STile	21mm x 21mm STile	4 – 11mm x 11mm STiles
195°C → 20°C	 1x Warpage	 0.76x Warpage	 0.72x Warpage
195°C → 260°C	 1x Warpage	 0.85X Warpage	 0.82X Warpage

► Presence of STile shows reduction in warpage

Conclusions

- ▶ Power delivery challenges require new innovations beyond Silicon
- ▶ The Saras STile addresses these challenges by:
 - ▶ Best in class Capacitance density and stability
 - ▶ Customizable Vertical Power Delivery Solution
 - ▶ Supports increased Si functionality
- ▶ STile Production in 2H of 2024
- ▶ Introduction of Inductor and Capacitor STile by 2025



Powering the Future

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